

Hideo Ohno

List of Publications by Year in descending order

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781
all docs

781
docs citations

781
times ranked

23532
citing authors

#	ARTICLE	IF	CITATIONS
1	Zener Model Description of Ferromagnetism in Zinc-Blende Magnetic Semiconductors. Science, 2000, 287, 1019-1022.	12.6	7,340
2	Making Nonmagnetic Semiconductors Ferromagnetic. , 1998, 281, 951-956.		4,503
3	A perpendicular-anisotropy CoFeB/MgO magnetic tunnel junction. Nature Materials, 2010, 9, 721-724.	27.5	3,020
4	Electrical spin injection in a ferromagnetic semiconductor heterostructure. Nature, 1999, 402, 790-792.	27.8	2,315
5	(Ga,Mn)As: A new diluted magnetic semiconductor based on GaAs. Applied Physics Letters, 1996, 69, 363-365.	3.3	2,213
6	Repeated temperature modulation epitaxy for p-type doping and light-emitting diode based on ZnO. Nature Materials, 2004, 4, 42-46.	27.5	1,963
7	Electric-field control of ferromagnetism. Nature, 2000, 408, 944-946.	27.8	1,904
8	Hole-mediated ferromagnetism in tetrahedrally coordinated semiconductors. Physical Review B, 2001, 63, .	3.2	1,439
9	Tunnel magnetoresistance of 604% at 300K by suppression of Ta diffusion in CoFeB/MgO/CoFeB pseudo-spin-valves annealed at high temperature. Applied Physics Letters, 2008, 93, .	3.3	1,259
10	Magnetotransport properties of p-type (In,Mn)As diluted magnetic III-V semiconductors. Physical Review Letters, 1992, 68, 2664-2667.	7.8	1,019
11	Diluted magnetic III-V semiconductors. Physical Review Letters, 1989, 63, 1849-1852.	7.8	1,018
12	Transport properties and origin of ferromagnetism in (Ga,Mn)As. Physical Review B, 1998, 57, R2037-R2040.	3.2	999
13	Current-induced torques in magnetic materials. Nature Materials, 2012, 11, 372-381.	27.5	969
14	Layer thickness dependence of the current-induced effective field vector in Ta CoFeB MgO. Nature Materials, 2013, 12, 240-245.	27.5	835
15	Magnetization switching by spin-orbit torque in an antiferromagnet/ferromagnet bilayer system. Nature Materials, 2016, 15, 535-541.	27.5	782
16	Properties of ferromagnetic III-V semiconductors. Journal of Magnetism and Magnetic Materials, 1999, 200, 110-129.	2.3	780
17	Dilute ferromagnetic semiconductors: Physics and spintronic structures. Reviews of Modern Physics, 2014, 86, 187-251.	45.6	772
18	Control of magnetism by electric fields. Nature Nanotechnology, 2015, 10, 209-220.	31.5	741

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19	Spintronics based random access memory: a review. <i>Materials Today</i> , 2017, 20, 530-548.	14.2	689
20	Current-induced domain-wall switching in a ferromagnetic semiconductor structure. <i>Nature</i> , 2004, 428, 539-542.	27.8	637
21	Magnetization vector manipulation by electric fields. <i>Nature</i> , 2008, 455, 515-518.	27.8	602
22	Electrical Manipulation of Magnetization Reversal in a Ferromagnetic Semiconductor. <i>Science</i> , 2003, 301, 943-945.	12.6	588
23	Quantum Hall Effect in Polar Oxide Heterostructures. <i>Science</i> , 2007, 315, 1388-1391.	12.6	531
24	A spin-orbit torque switching scheme with collinear magnetic easy axis and current configuration. <i>Nature Nanotechnology</i> , 2016, 11, 621-625.	31.5	466
25	Magnetic Tunnel Junctions for Spintronic Memories and Beyond. <i>IEEE Transactions on Electron Devices</i> , 2007, 54, 991-1002.	3.0	460
26	Electric-field effects on thickness dependent magnetic anisotropy of sputtered MgO/Co ₄₀ Fe ₄₀ B ₂₀ /Ta structures. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	443
27	Unified disorder induced gap state model for insulator-semiconductor and metal-semiconductor interfaces. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1986, 4, 1130.	1.6	441
28	Quantitative characterization of the spin-orbit torque using harmonic Hall voltage measurements. <i>Physical Review B</i> , 2014, 89, .	3.2	415
29	Blue Light-Emitting Diode Based on ZnO. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L643-L645.	1.5	408
30	Spin Relaxation in GaAs(110) Quantum Wells. <i>Physical Review Letters</i> , 1999, 83, 4196-4199.	7.8	389
31	Electric field-induced magnetization reversal in a perpendicular-anisotropy CoFeB-MgO magnetic tunnel junction. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	341
32	Interface control of the magnetic chirality in CoFeB/MgO heterostructures with heavy-metal underlayers. <i>Nature Communications</i> , 2014, 5, 4655.	12.8	327
33	Fabrication of a Nonvolatile Full Adder Based on Logic-in-Memory Architecture Using Magnetic Tunnel Junctions. <i>Applied Physics Express</i> , 0, 1, 091301.	2.4	302
34	Spin transport and spin torque in antiferromagnetic devices. <i>Nature Physics</i> , 2018, 14, 220-228.	16.7	298
35	Integer factorization using stochastic magnetic tunnel junctions. <i>Nature</i> , 2019, 573, 390-393.	27.8	298
36	Effect of electrode composition on the tunnel magnetoresistance of pseudo-spin-valve magnetic tunnel junction with a MgO tunnel barrier. <i>Applied Physics Letters</i> , 2007, 90, 212507.	3.3	293

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37	Modeling and simulation of polycrystalline ZnO thin-film transistors. Journal of Applied Physics, 2003, 94, 7768.	2.5	284
38	High Mobility Thin Film Transistors with Transparent ZnO Channels. Japanese Journal of Applied Physics, 2003, 42, L347-L349.	1.5	267
39	Spin-transfer torque RAM technology: Review and prospect. Microelectronics Reliability, 2012, 52, 613-627.	1.7	265
40	Magnetic Circular Dichroism Studies of Carrier-Induced Ferromagnetism in $(\text{Ga}_{1-x}\text{Mn}_x)\text{As}$. Physical Review Letters, 1999, 83, 3073-3076.	7.8	258
41	Observation of the fractional quantum Hall effect in an oxide. Nature Materials, 2010, 9, 889-893.	27.5	258
42	A window on the future of spintronics. Nature Materials, 2010, 9, 952-954.	27.5	257
43	Perpendicular-anisotropy CoFeB-MgO magnetic tunnel junctions with a MgO/CoFeB/Ta/CoFeB/MgO recording structure. Applied Physics Letters, 2012, 101, .	3.3	255
44	Dependence of Giant Tunnel Magnetoresistance of Sputtered CoFeB/MgO/CoFeB Magnetic Tunnel Junctions on MgO Barrier Thickness and Annealing Temperature. Japanese Journal of Applied Physics, 2005, 44, L587-L589.	1.5	242
45	Properties of magnetic tunnel junctions with a MgO/CoFeB/Ta/CoFeB/MgO recording structure down to junction diameter of 11 nm. Applied Physics Letters, 2014, 105, .	3.3	240
46	Effect of low-temperature annealing on $(\text{Ga},\text{Mn})\text{As}$ trilayer structures. Applied Physics Letters, 2003, 82, 3020-3022.	3.3	220
47	Single-Shot Time-Resolved Measurements of Nanosecond-Scale Spin-Transfer Induced Switching: Stochastic Versus Deterministic Aspects. Physical Review Letters, 2008, 100, 057206.	7.8	219
48	Velocity of Domain-Wall Motion Induced by Electrical Current in the Ferromagnetic Semiconductor $(\text{Ga},\text{Mn})\text{As}$. Physical Review Letters, 2006, 96, 096601.	7.8	218
49	2 Mb SPRAM (Spin-Transfer Torque RAM) With Bit-by-Bit Bi-Directional Current Write and Parallelizing-Direction Current Read. IEEE Journal of Solid-State Circuits, 2008, 43, 109-120.	5.4	212
50	Experimental probing of the interplay between ferromagnetism and localization in $(\text{Ga},\text{Mn})\text{As}$. Nature Physics, 2010, 6, 22-25.	16.7	211
51	Effect of high annealing temperature on giant tunnel magnetoresistance ratio of CoFeB/MgO/CoFeB magnetic tunnel junctions. Applied Physics Letters, 2006, 89, 232510.	3.3	205
52	Mott Relation for Anomalous Hall and Nernst Effects in $\text{Ga}_{1-x}\text{Mn}_x$ Semiconductors. Physical Review Letters, 2008, 101, 117208.	7.8	204
53	Room-temperature ferromagnetism in zincblende CrSb grown by molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 2776-2778.	3.3	203
54	Epitaxy of $(\text{Ga}, \text{Mn})\text{As}$, a new diluted magnetic semiconductor based on GaAs. Journal of Crystal Growth, 1997, 175-176, 1069-1074.	1.5	183

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55	Current-Driven Magnetization Switching in CoFeB/MgO/CoFeB Magnetic Tunnel Junctions. Japanese Journal of Applied Physics, 2005, 44, L1267.	1.5	182
56	A ferromagnetic III-V semiconductor: (Ga,Mn)As. Solid State Communications, 2001, 117, 179-186.	1.9	178
57	Observation of π -Tamm states in superlattices. Physical Review Letters, 1990, 64, 2555-2558.	7.8	171
58	Spin-orbit torque induced magnetization switching in nano-scale Ta/CoFeB/MgO. Applied Physics Letters, 2015, 107, .	3.3	167
59	SEMICONDUCTORS: Enhanced: Toward Functional Spintronics. Science, 2001, 291, 840-841.	12.6	165
60	Formation and current-induced motion of synthetic antiferromagnetic skyrmion bubbles. Nature Communications, 2019, 10, 5153.	12.8	165
61	Nonmetal-metal-nonmetal transition and large negative magnetoresistance in (Ga, Mn)As/GaAs. Solid State Communications, 1997, 103, 209-213.	1.9	150
62	Giant tunnel magnetoresistance and high annealing stability in CoFeB/MgO/CoFeB magnetic tunnel junctions with synthetic pinned layer. Applied Physics Letters, 2006, 89, 042506.	3.3	150
63	Electric-field control of ferromagnetism in (Ga,Mn)As. Applied Physics Letters, 2006, 89, 162505.	3.3	149
64	Spontaneous splitting of ferromagnetic (Ga, Mn)As valence band observed by resonant tunneling spectroscopy. Applied Physics Letters, 1998, 73, 363-365.	3.3	147
65	New III-V diluted magnetic semiconductors (invited). Journal of Applied Physics, 1991, 69, 6103-6108.	2.5	146
66	Analogue spin-orbit torque device for artificial-neural-network-based associative memory operation. Applied Physics Express, 2017, 10, 013007.	2.4	146
67	Antiferromagnetic d-d exchange in ferromagnetic Ga _{1-x} Mn _x As epilayers. Physical Review B, 1999, 59, 12935-12939.	3.2	145
68	Magnetoresistance effect and interlayer coupling of (Ga, \check{S} Mn)As trilayer structures. Applied Physics Letters, 2000, 77, 1873.	3.3	143
69	Junction size effect on switching current and thermal stability in CoFeB/MgO perpendicular magnetic tunnel junctions. Applied Physics Letters, 2011, 99, .	3.3	143
70	Optical Manipulation of Nuclear Spin by a Two-Dimensional Electron Gas. Physical Review Letters, 2001, 86, 2677-2680.	7.8	142
71	Shape anisotropy revisited in single-digit nanometer magnetic tunnel junctions. Nature Communications, 2018, 9, 663.	12.8	141
72	Current-Driven Magnetization Reversal in a Ferromagnetic Semiconductor (Ga,Mn)As/GaAs/(Ga,Mn)As Tunnel Junction. Physical Review Letters, 2004, 93, 216602.	7.8	140

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73	Character of states near the Fermi level in (Ga,Mn)As: Impurity to valence band crossover. Physical Review B, 2007, 76, .	3.2	139
74	Current-induced domain wall motion in perpendicularly magnetized CoFeB nanowire. Applied Physics Letters, 2011, 98, .	3.3	135
75	Current-induced effective field in perpendicularly magnetized Ta/CoFeB/MgO wire. Applied Physics Letters, 2011, 98, .	3.3	133
76	Universality Classes for Domain Wall Motion in the Ferromagnetic Semiconductor (Ga,Mn)As. Science, 2007, 317, 1726-1729.	12.6	130
77	MgO barrier-perpendicular magnetic tunnel junctions with CoFe/Pd multilayers and ferromagnetic insertion layers. Applied Physics Letters, 2009, 95, .	3.3	130
78	A Spin Esaki Diode. Japanese Journal of Applied Physics, 2001, 40, L1274-L1276.	1.5	125
79	Current-Induced Magnetization Switching in MgO Barrier Based Magnetic Tunnel Junctions with CoFeB/Ru/CoFeB Synthetic Ferrimagnetic Free Layer. Japanese Journal of Applied Physics, 2006, 45, L1057-L1060.	1.5	125
80	Domain Structure in CoFeB Thin Films With Perpendicular Magnetic Anisotropy. IEEE Magnetics Letters, 2011, 2, 3000304-3000304.	1.1	124
81	Artificial Neuron and Synapse Realized in an Antiferromagnet/Ferromagnet Heterostructure Using Dynamics of Spin-Orbit Torque Switching. Advanced Materials, 2019, 31, e1900636.	21.0	124
82	Tunneling magnetoresistance in (Ga,Mn)As-based heterostructures with a GaAs barrier. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 966-969.	2.7	122
83	An Overview of Nonvolatile Emerging Memories—Spintronics for Working Memories. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2016, 6, 109-119.	3.6	121
84	Magnetotransport properties of metallic (Ga,Mn)As films with compressive and tensile strain. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 1032-1036.	2.7	120
85	MgO/CoFeB/Ta/CoFeB/MgO Recording Structure in Magnetic Tunnel Junctions With Perpendicular Easy Axis. IEEE Transactions on Magnetics, 2013, 49, 4437-4440.	2.1	120
86	Magnetotransport properties of (Ga,Mn)As investigated at low temperature and high magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 976-980.	2.7	117
87	Enhanced interface perpendicular magnetic anisotropy in Ta CoFeB MgO using nitrogen doped Ta underlayers. Applied Physics Letters, 2013, 102, .	3.3	117
88	A 32-Mb SPRAM With 2T1R Memory Cell, Localized Bi-Directional Write Driver and '1/0' Dual-Array Equalized Reference Scheme. IEEE Journal of Solid-State Circuits, 2010, 45, 869-879.	5.4	115
89	chapter 1 III-V Ferromagnetic Semiconductors. Handbook of Magnetic Materials, 2002, 14, 1-87.	0.6	112
90	Semiconductor spintronics. IEEE Nanotechnology Magazine, 2002, 1, 19-31.	2.0	112

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91	Electronic and microstructural properties of disorder-induced gap states at compound semiconductor-insulator interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 1097.	1.6	110
92	Dependence of magnetic anisotropy on MgO thickness and buffer layer in Co ₂₀ Fe ₆₀ B ₂₀ -MgO structure. Journal of Applied Physics, 2011, 109, .	2.5	109
93	Arsenic stabilization of InP substrates for growth of GaIn _{1-x} As layers by molecular beam epitaxy. Applied Physics Letters, 1980, 37, 290-292.	3.3	106
94	2Mb Spin-Transfer Torque RAM (SPRAM) with Bit-by-Bit Bidirectional Current Write and Parallelizing-Direction Current Read. , 2007, , .		106
95	Electric-field effects on magnetic anisotropy and damping constant in Ta/CoFeB/MgO investigated by ferromagnetic resonance. Applied Physics Letters, 2014, 105, .	3.3	106
96	Phase Transition in the $\nu=2$ Bilayer Quantum Hall State. Physical Review Letters, 1998, 80, 4534-4537.	7.8	104
97	Standby-Power-Free Integrated Circuits Using MTJ-Based VLSI Computing. Proceedings of the IEEE, 2016, 104, 1844-1863.	21.3	102
98	Ferromagnetic III-V and II-VI Semiconductors. MRS Bulletin, 2003, 28, 714-719.	3.5	101
99	Dependence of Tunnel Magnetoresistance in MgO Based Magnetic Tunnel Junctions on Ar Pressure during MgO Sputtering. Japanese Journal of Applied Physics, 2005, 44, L1442-L1445.	1.5	99
100	Three terminal magnetic tunnel junction utilizing the spin Hall effect of iridium-doped copper. Applied Physics Letters, 2013, 102, .	3.3	99
101	Origin of enhanced dynamic nuclear polarization and all-optical nuclear magnetic resonance in GaAs quantum wells. Physical Review B, 2001, 64, .	3.2	96
102	Anomalous temperature dependence of current-induced torques in CoFeB/MgO with Ta-based underlayers. Physical Review B, 2014, 89, .	1.2	96
103	CoFeB Thickness Dependence of Thermal Stability Factor in CoFeB/MgO Perpendicular Magnetic Tunnel Junctions. IEEE Magnetics Letters, 2012, 3, 3000204-3000204.	1.1	92
104	On the origin and elimination of macroscopic defects in MBE films. Journal of Crystal Growth, 1981, 51, 299-303.	1.5	91
105	Direct-current voltages in (Ga,Mn)As structures induced by ferromagnetic resonance. Nature Communications, 2013, 4, 2055.	12.8	87
106	Magnetization switching in a CoFeB/MgO magnetic tunnel junction by combining spin-transfer torque and electric field-effect. Applied Physics Letters, 2014, 104, .	3.3	87
107	Chiral-spin rotation of non-collinear antiferromagnet by spin-orbit torque. Nature Materials, 2021, 20, 1364-1370.	27.5	87
108	Electronic Properties and Modeling of Lattice-Mismatched and Regrown GaAs Interfaces Prepared by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1988, 27, 180-187.	1.5	86

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109	Atomic-Scale Structure and Local Chemistry of CoFeB/MgO Magnetic Tunnel Junctions. Nano Letters, 2016, 16, 1530-1536.	9.1	85
110	Magnetic moment of Mn in the ferromagnetic semiconductor (Ga _{0.98} Mn _{0.02})As. Applied Physics Letters, 2000, 76, 2928-2930.	3.3	84
111	Ferromagnetism of magnetic semiconductors: Zhang-Rice limit. Physical Review B, 2002, 66, .	3.2	84
112	Electric-field-induced magnetization switching in CoFeB/MgO magnetic tunnel junctions with high junction resistance. Applied Physics Letters, 2016, 108, .	3.3	84
113	Current-Induced Magnetization Switching in MgO Barrier Magnetic Tunnel Junctions With CoFeB-Based Synthetic Ferrimagnetic Free Layers. IEEE Transactions on Magnetics, 2008, 44, 1962-1967.	2.1	83
114	A multi-level-cell spin-transfer torque memory with series-stacked magnetotunnel junctions. , 2010, , .		83
115	Control of Fermi level pinning and recombination processes at GaAs surfaces by chemical and photochemical treatments. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1184.	1.6	82
116	GaInAs/AlInAs structures grown by molecular beam epitaxy. Journal of Applied Physics, 1981, 52, 4033-4037.	2.5	81
117	GaAs and In _{0.53} Ga _{0.47} As MIS Structures Having an Ultrathin Pseudomorphic Interface Control Layer of Si Prepared by MBE. Japanese Journal of Applied Physics, 1988, 27, L2265-L2267.	1.5	81
118	Magnetotransport properties of (Ga, $\tilde{\text{Mn}}$)Sb. Journal of Applied Physics, 2000, 87, 6442-6444.	2.5	81
119	Transmission electron microscopy investigation of CoFeB/MgO/CoFeB pseudospin valves annealed at different temperatures. Journal of Applied Physics, 2009, 106, .	2.5	81
120	Magnetic and transport properties of the ferromagnetic semiconductor heterostructures (In,Mn)As/(Ga,Al)Sb. Physical Review B, 1999, 59, 5826-5831.	3.2	80
121	Spin-dependent tunneling and properties of ferromagnetic (Ga,Mn)As (invited). Journal of Applied Physics, 1999, 85, 4277-4282.	2.5	80
122	Molecular beam epitaxy of III $\tilde{\text{V}}$ diluted magnetic semiconductor (Ga,Mn)Sb. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 981-985.	2.7	78
123	Spin-orbit torques in high-resistivity-W/CoFeB/MgO. Applied Physics Letters, 2018, 112, .	3.3	77
124	Generation and control of polarization-entangled photons from GaAs island quantum dots by an electric field. Nature Communications, 2012, 3, 661.	12.8	76
125	Observation of magnetic domain structure in a ferromagnetic semiconductor (Ga, $\tilde{\text{Mn}}$)As with a scanning Hall probe microscope. Applied Physics Letters, 2000, 77, 1363-1365.	3.3	74
126	Standby-Power-Free Compact Ternary Content-Addressable Memory Cell Chip Using Magnetic Tunnel Junction Devices. Applied Physics Express, 0, 2, 023004.	2.4	73

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127	Engineering magnetism in semiconductors. <i>Materials Today</i> , 2006, 9, 18-26.	14.2	72
128	Properties of $\text{Ga}_{1-x}\text{Mn}_x\text{As}$ with high Mn composition ($x>0.1$). <i>Applied Physics Letters</i> , 2007, 90, 122503.	3.3	72
129	Antiferromagnetism in hcp Iron-Manganese Alloys. <i>Journal of the Physical Society of Japan</i> , 1971, 31, 102-108.	1.6	71
130	Spatially homogeneous ferromagnetism of (Ga, Mn)As. <i>Nature Materials</i> , 2010, 9, 299-303.	27.5	71
131	Modeling of grain boundary barrier modulation in ZnO invisible thin film transistors. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 21, 911-915.	2.7	70
132	A 1 Mb Nonvolatile Embedded Memory Using 4T2MTJ Cell With 32 b Fine-Grained Power Gating Scheme. <i>IEEE Journal of Solid-State Circuits</i> , 2013, 48, 1511-1520.	5.4	70
133	A self-consistent computer simulation of compound semiconductor metal-insulator-semiconductor curves based on the disorder-induced gap state model. <i>Journal of Applied Physics</i> , 1988, 63, 2120-2130.	2.5	69
134	Curie temperature versus hole concentration in field-effect structures of $\text{Ga}_{1-x}\text{Mn}_x\text{As}$. <i>Physical Review B</i> , 2010, 81, .	3.2	69
135	Critical role of W deposition condition on spin-orbit torque induced magnetization switching in nanoscale W/CoFeB/MgO. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	69
136	Electron mobility exceeding $10^4 \text{ cm}^2/\text{Vs}$ in an AlGaIn/GaN heterostructure grown on a sapphire substrate. <i>Applied Physics Letters</i> , 1999, 74, 3531-3533.	3.3	68
137	Anomalous Hall Effect in Field-Effect Structures of (Ga,Mn)As. <i>Physical Review Letters</i> , 2010, 104, 106601.	7.8	68
138	Perspective: Spintronic synapse for artificial neural network. <i>Journal of Applied Physics</i> , 2018, 124, .	2.5	67
139	Ferromagnetism in III-V and II-VI semiconductor structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001, 9, 185-193.	2.7	66
140	Detection of single magnetic bead for biological applications using an InAs quantum-well micro-Hall sensor. <i>Applied Physics Letters</i> , 2005, 87, 112502.	3.3	66
141	Magnetic tunnel junction for nonvolatile CMOS logic. , 2010, , .		66
142	Device-size dependence of field-free spin-orbit torque induced magnetization switching in antiferromagnet/ferromagnet structures. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	66
143	Hall magnetometry on a single iron nanoparticle. <i>Applied Physics Letters</i> , 2002, 80, 4644-4646.	3.3	65
144	Domain-Wall Resistance in Ferromagnetic (Ga,Mn)As. <i>Physical Review Letters</i> , 2006, 96, 096602.	7.8	65

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145	New diluted magnetic semiconductors based on III-V compounds. Journal of Magnetism and Magnetic Materials, 1991, 93, 356-364.	2.3	64
146	Metal-insulator transition and magnetotransport in III-V compound diluted magnetic semiconductors. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 63, 88-95.	3.5	64
147	Observation of boron diffusion in an annealed Ta/CoFeB/MgO magnetic tunnel junction with standing-wave hard x-ray photoemission. Applied Physics Letters, 2012, 101, .	3.3	64
148	Nanosecond Random Telegraph Noise in In-Plane Magnetic Tunnel Junctions. Physical Review Letters, 2021, 126, 117202.	7.8	64
149	P-Type diluted magnetic III-V semiconductors. Journal of Crystal Growth, 1991, 111, 1011-1015.	1.5	63
150	RECENT PROGRESS OF PERPENDICULAR ANISOTROPY MAGNETIC TUNNEL JUNCTIONS FOR NONVOLATILE VLSI. Spin, 2012, 02, 1240003.	1.3	63
151	10.5 A 90nm 20MHz fully nonvolatile microcontroller for standby-power-critical applications. , 2014, , .		63
152	Memristive control of mutual spin Hall nano-oscillator synchronization for neuromorphic computing. Nature Materials, 2022, 21, 81-87.	27.5	63
153	MTJ-based nonvolatile logic-in-memory circuit, future prospects and issues. , 2009, , .		62
154	InAs/AlSb quantum cascade lasers operating at 10 μ m. Applied Physics Letters, 2003, 82, 1003-1005.	3.3	61
155	Current induced effective magnetic field and magnetization reversal in uniaxial anisotropy (Ga,Mn)As. Applied Physics Letters, 2010, 97, .	3.3	61
156	A nondestructive analysis of the B diffusion in Ta-CoFeB-MgO-CoFeB-Ta magnetic tunnel junctions by hard x-ray photoemission. Applied Physics Letters, 2010, 96, .	3.3	60
157	Magnetophonon Resonance in a Two-Dimensional Electron System in the GaAs-Al _x Ga _{1-x} As Heterojunction Interface. Journal of the Physical Society of Japan, 1982, 51, 2168-2173.	1.6	59
158	Resonant interband tunneling via Landau levels in polytype heterostructures. Physical Review B, 1991, 43, 5196-5199.	3.2	59
159	Integrated micromechanical cantilever magnetometry of Ga _{1-x} MnxAs. Applied Physics Letters, 1999, 75, 1140-1142.	3.3	57
160	Magnetic properties of (Al,Ga,Mn)As. Applied Physics Letters, 2002, 81, 2590-2592.	3.3	57
161	Relaxation of photoinjected spins during drift transport in GaAs. Applied Physics Letters, 2002, 81, 2788-2790.	3.3	56
162	High-Mobility Field-Effect Transistors Based on Single-Crystalline ZnO Channels. Japanese Journal of Applied Physics, 2005, 44, L1193-L1195.	1.5	56

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163	Epitaxy of III-V diluted magnetic semiconductor materials. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 176.	1.6	55
164	Origin of the collapse of tunnel magnetoresistance at high annealing temperature in CoFeB/MgO perpendicular magnetic tunnel junctions. Applied Physics Letters, 2011, 99, .	3.3	55
165	Antiferromagnetism of Dilute Cr Alloys with Co and Ni. Journal of the Physical Society of Japan, 1968, 24, 263-270.	1.6	54
166	Magnetism of Co-doped ZnO epitaxially grown on a ZnO substrate. Physical Review B, 2012, 85, .	3.2	54
167	Interlayer exchange in (Ga,Mn)As/(Al,Ga)As/(Ga,Mn)As semiconducting ferromagnet/nonmagnet/ferromagnet trilayer structures. Applied Physics Letters, 1998, 73, 2122-2124.	3.3	53
168	Anisotropic electrical spin injection in ferromagnetic semiconductor heterostructures. Applied Physics Letters, 2002, 80, 1598-1600.	3.3	53
169	Intersubband transitions in ZnO multiple quantum wells. Applied Physics Letters, 2008, 92, .	3.3	53
170	In-plane magnetic field dependence of electric field-induced magnetization switching. Applied Physics Letters, 2013, 103, .	3.3	53
171	Nonvolatile Logic-in-Memory LSI Using Cycle-Based Power Gating and its Application to Motion-Vector Prediction. IEEE Journal of Solid-State Circuits, 2015, 50, 476-489.	5.4	53
172	Electric field control of Skyrmions in magnetic nanodisks. Applied Physics Letters, 2016, 108, .	3.3	53
173	Tunnel magnetoresistance in MgO-barrier magnetic tunnel junctions with bcc-CoFe(B) and fcc-CoFe free layers. Journal of Applied Physics, 2006, 99, 08A907.	2.5	52
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